



TM04P02AI

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

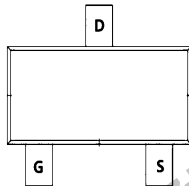
$V_{DS} = -20V, I_D = -4.0A$

$R_{DS(ON)} = 29 m\Omega$ (Typ.) @ $V_{GS} = -4.5V$

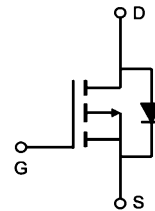
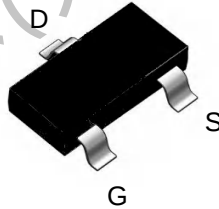
100% UIS Tested
100% R_g Tested



I: SOT-23



Marking: 3415



Absolute Maximum Ratings $T_A = 25^\circ C$ un (less otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-4.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-3.0	A
I_{DM}	Pulsed Drain Current ²	-26	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	3.9	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation ³	0.84	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ C/W$

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.014	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V$, $I_D=-4.9A$	---	29	35	$m\Omega$
		$V_{GS}=-2.5V$, $I_D=-3.4A$	---	36	42	
		$V_{GS}=-1.8V$, $I_D=-2A$	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-0.4	-0.65	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.95	---	mV/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-3A$	---	12.8	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-3A$	---	9.2	14.3	nC
Q_{gs}	Gate-Source Charge		---	1.89	2.6	
Q_{gd}	Gate-Drain Charge		---	3.1	4.3	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V$, $V_{GS}=-4.5V$, $R_G=3.3\Omega$, $I_D=-3A$	---	5.6	11.2	ns
T_r	Rise Time		---	40.8	73	
$T_{d(off)}$	Turn-Off Delay Time		---	33.6	67	
T_f	Fall Time		---	18	36	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	757	1200	pF
C_{oss}	Output Capacitance		---	104	160	
C_{rss}	Reverse Transfer Capacitance		---	98	151	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-4.0	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-10	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^{\circ}\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-3A$, $di/dt=100A/\mu s$,	---	21.8	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^{\circ}\text{C}$	---	6.9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Performance Characteristics

Figure1: Output Characteristics

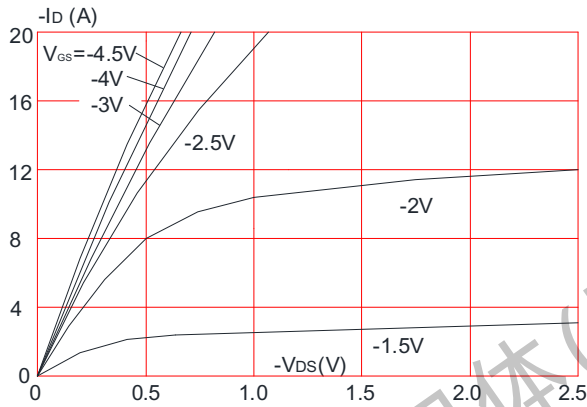


Figure 2: Typical Transfer Characteristics

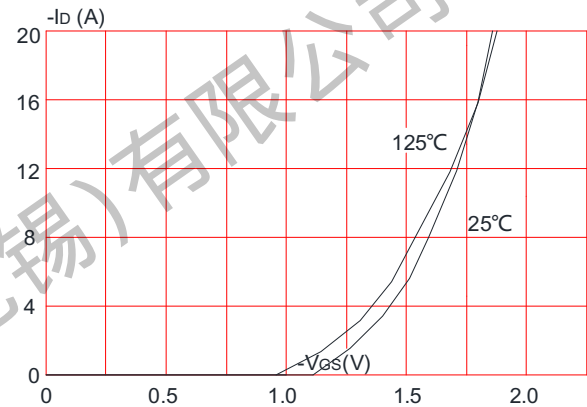


Figure 3: On-resistance vs. Drain Current

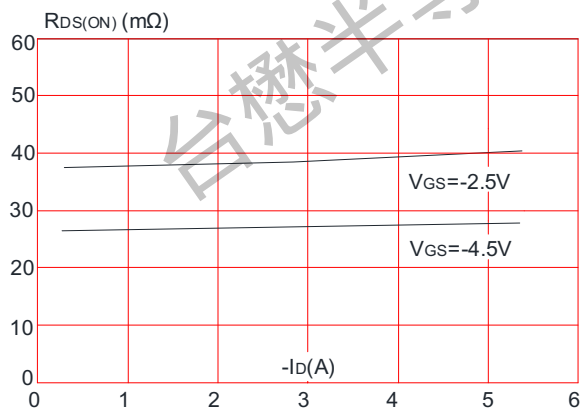


Figure 4: Body Diode Characteristics

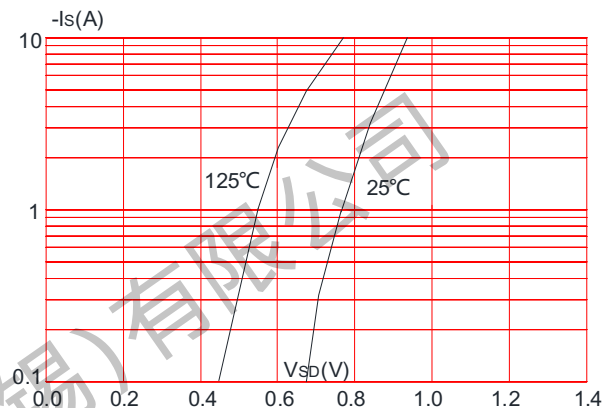


Figure 5: Gate Charge Characteristics

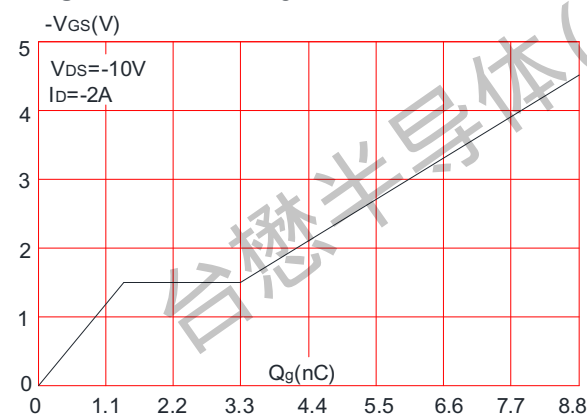
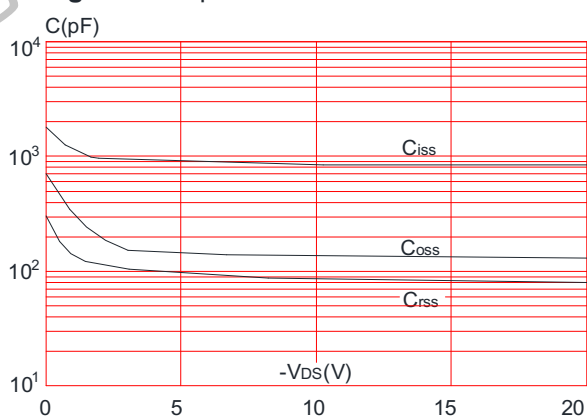


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

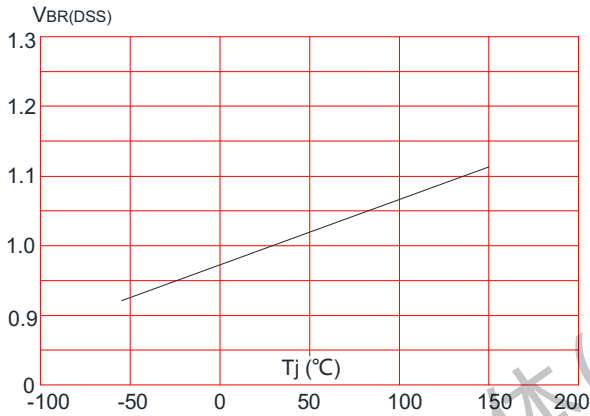


Figure 8: Normalized on Resistance vs. Junction Temperature

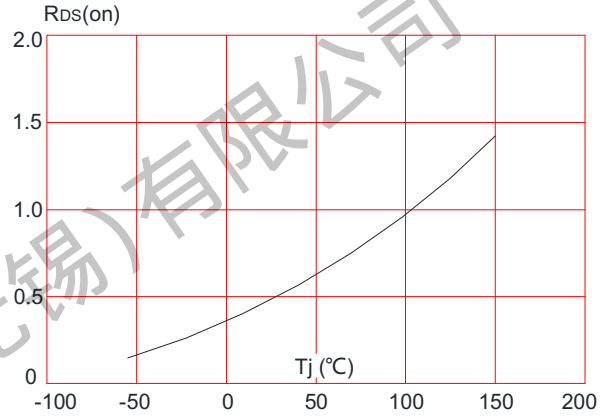


Figure 9: Maximum Safe Operating Area

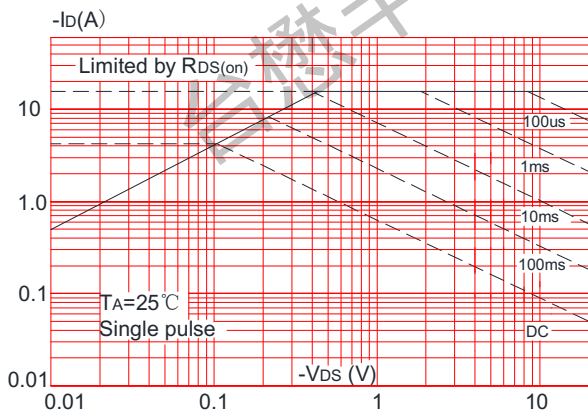


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

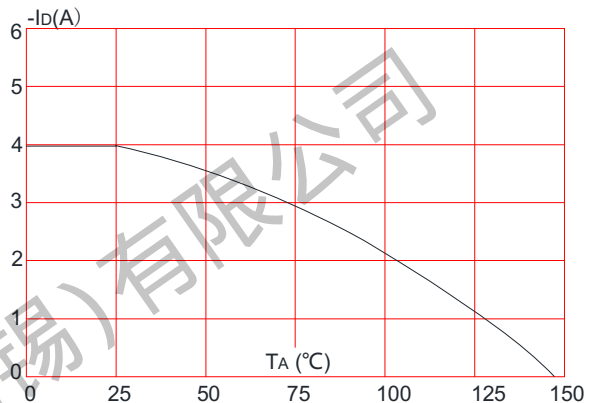
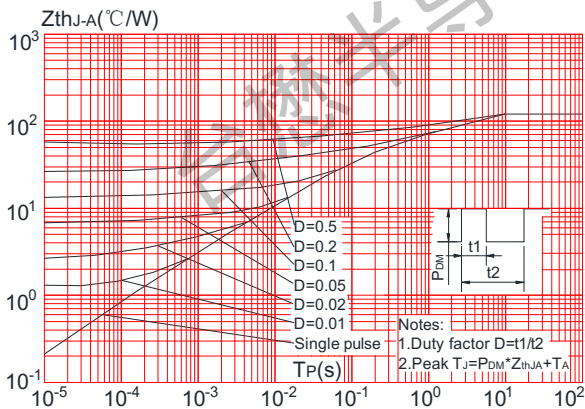


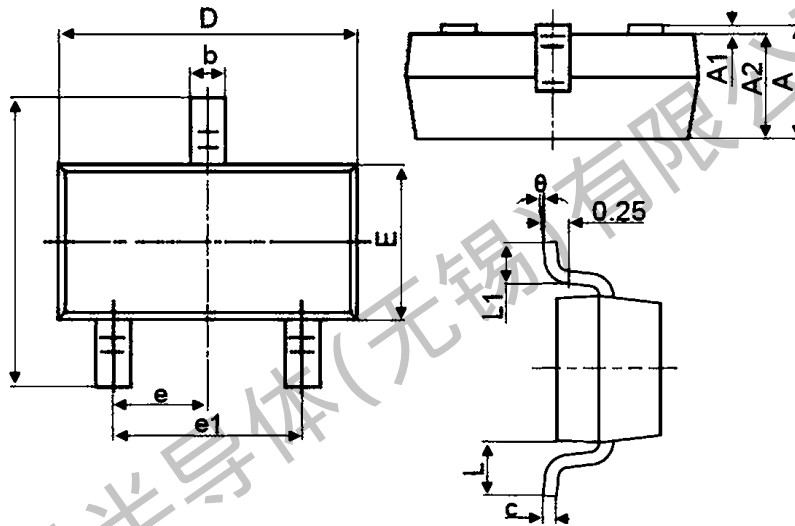
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



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Package Mechanical Data:SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

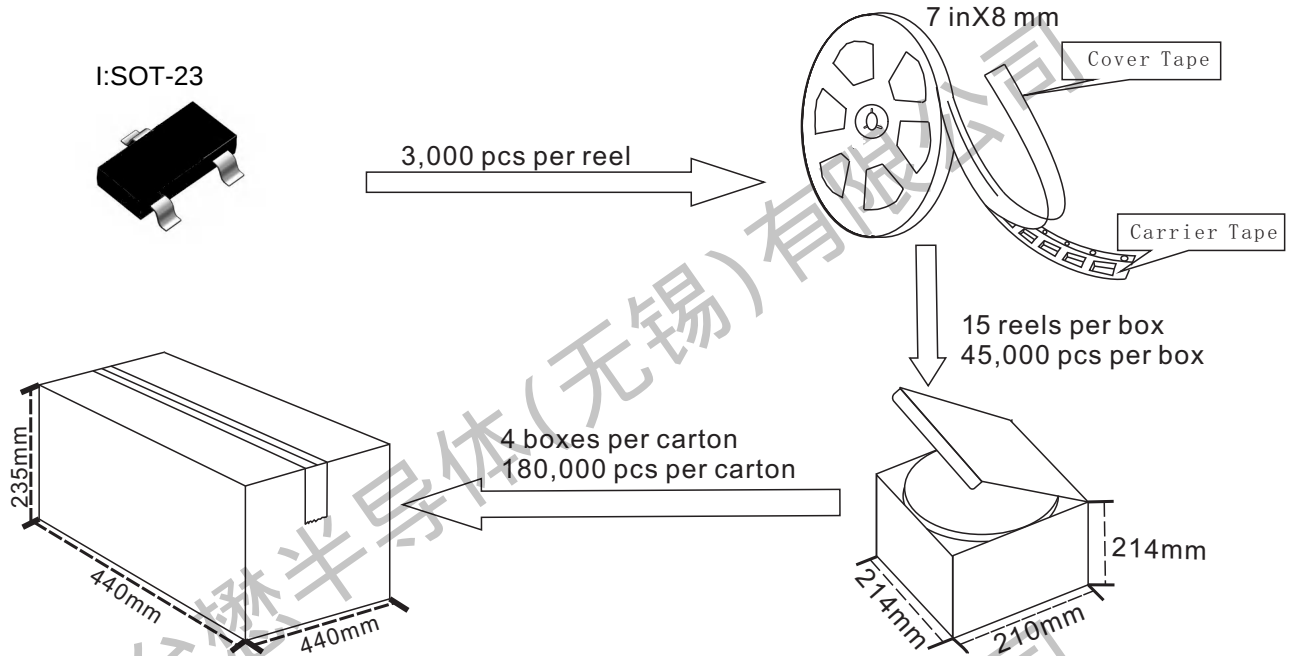


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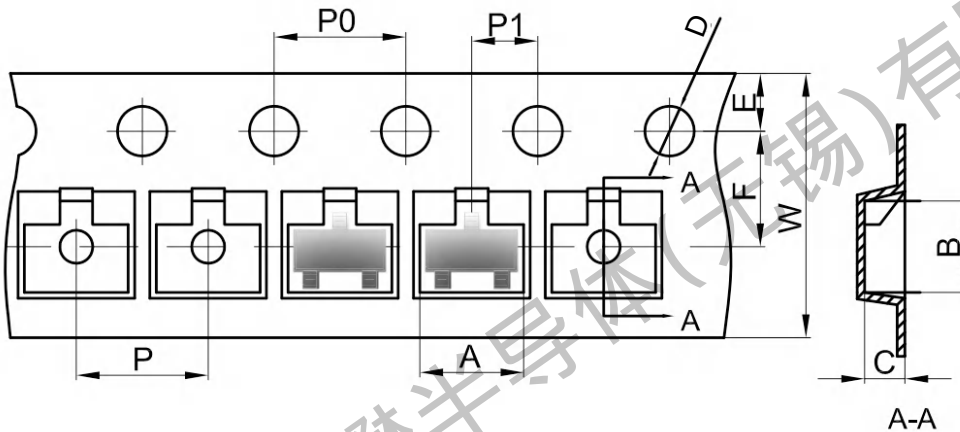
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SOT-23 Packing

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)



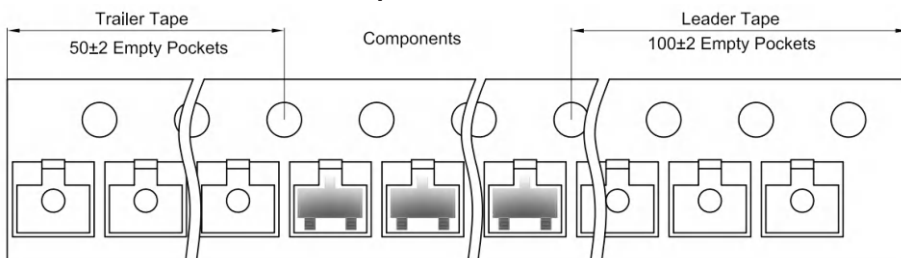
SOT-23 Embossed Carrier Tape



Dimensions are in millimeter

Pkg type	A	B	C	D	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



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Revision history:

Date	Rev	Description	Page
2023.05.05	23.05	Original	